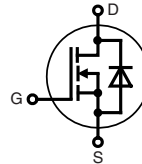


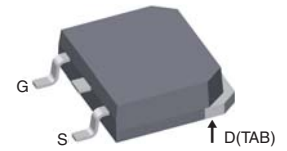
CoolMOS™¹⁾ Power MOSFET

N-Channel Enhancement Mode
Low $R_{DS(on)}$, High V_{DSS} MOSFET
Ultra low gate charge

$$\begin{aligned} I_{D25} &= 66 \text{ A} \\ V_{DSS} &= 600 \text{ V} \\ R_{DS(on) \text{ max}} &= 0.045 \Omega \end{aligned}$$



TO-268 AA



MOSFET			
Symbol	Conditions	Maximum Ratings	
V_{DSS}	$T_{VJ} = 25^\circ\text{C}$	600	V
V_{GS}		± 20	V
I_{D25}	$T_C = 25^\circ\text{C}$	66	A
I_{D90}	$T_C = 90^\circ\text{C}$	46	A
E_{AS} E_{AR}	single pulse repetitive } $I_D = 11 \text{ A}; T_C = 25^\circ\text{C}$	1950 3	mJ mJ
dV/dt	MOSFET dV/dt ruggedness $V_{DS} = 0 \dots 480 \text{ V}$	50	V/ns

Features

- fast CoolMOS™¹⁾ power MOSFET 4th generation
- High blocking capability
- Lowest resistance
- Avalanche rated for unclamped inductive switching (UIS)
- Low thermal resistance due to reduced chip thickness
- Enhanced total power density

Applications

- Switched mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)
- Power factor correction (PFC)
- Welding
- Inductive heating
- PDP and LCD adapter

¹⁾ CoolMOS™ is a trademark of Infineon Technologies AG.

Symbol	Conditions	Characteristic Values			
		$(T_{VJ} = 25^\circ\text{C}, \text{ unless otherwise specified})$			
		min.	typ.	max.	
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}; I_D = 44 \text{ A}$		40	45	mΩ
$V_{GS(th)}$	$V_{DS} = V_{GS}; I_D = 3 \text{ mA}$	2.5	3	3.5	V
I_{DSS}	$V_{DS} = 600 \text{ V}; V_{GS} = 0 \text{ V}$			10	μA
	$T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$		50		μA
I_{GSS}	$V_{GS} = \pm 20 \text{ V}; V_{DS} = 0 \text{ V}$			100	nA
C_{iss} C_{oss}	$V_{GS} = 0 \text{ V}; V_{DS} = 100 \text{ V}$ $f = 1 \text{ MHz}$		6800 320		pF pF
Q_g Q_{gs} Q_{gd}	$V_{GS} = 0 \text{ to } 10 \text{ V}; V_{DS} = 400 \text{ V}; I_D = 44 \text{ A}$		150 35 50	190	nC nC nC
$t_{d(on)}$ t_r $t_{d(off)}$ t_f	$V_{GS} = 10 \text{ V}; V_{DS} = 400 \text{ V}$ $I_D = 44 \text{ A}; R_G = 3.3 \Omega$		30 20 100 10		ns ns ns ns
R_{thJC}				0.23	K/W

Source-Drain Diode

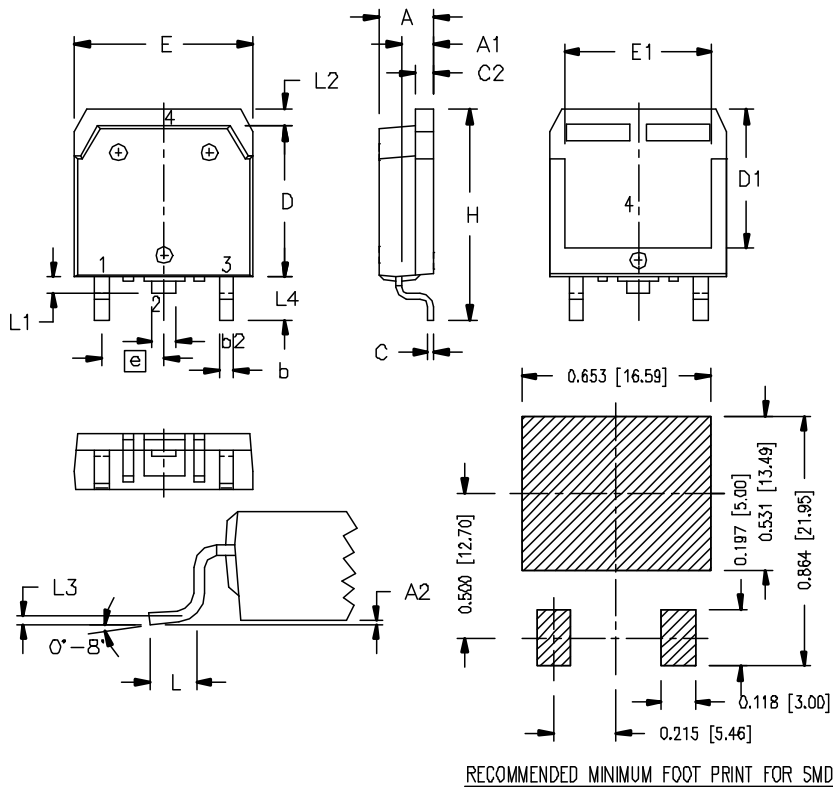
Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
I_S	$V_{GS} = 0\text{ V}$			44 A
V_{SD}	$I_F = 44\text{ A}; V_{GS} = 0\text{ V}$	0.9	1.2	V
t_{rr}	$I_F = 44\text{ A}; -di_F/dt = 100\text{ A}/\mu\text{s}; V_R = 400\text{ V}$	600		ns
Q_{RM}		17		μC
I_{RM}		60		A

Component

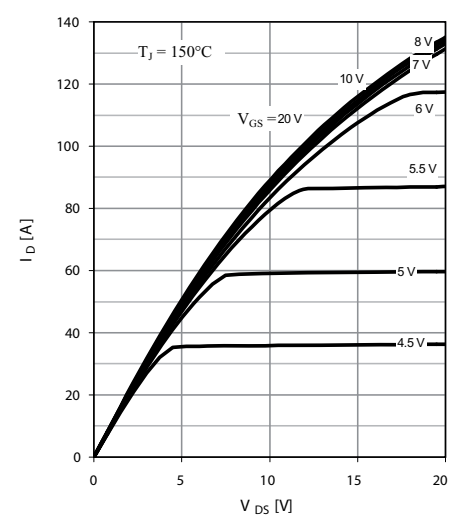
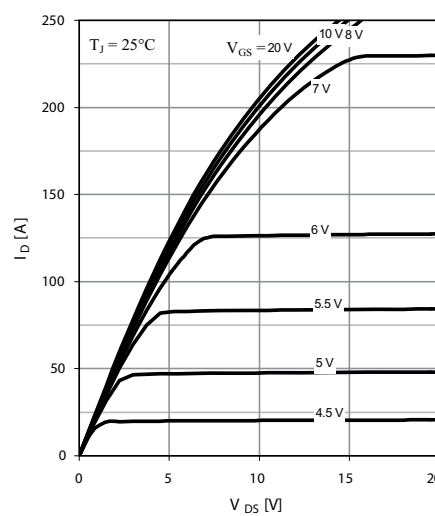
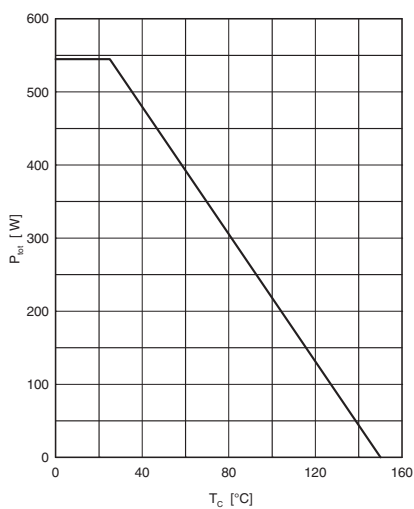
Symbol	Conditions	Maximum Ratings	
T_{VJ}	operating	-55...+150	$^{\circ}\text{C}$
T_{stg}		-55...+150	$^{\circ}\text{C}$

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
Weight			6	g

TO-247 AD Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A1	.106	.114	2.70	2.90
A2	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
b2	.075	.083	1.90	2.10
C	.016	.026	0.40	0.65
C2	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D1	.488	.500	12.40	12.70
E	.624	.632	15.85	16.05
E1	.524	.535	13.30	13.60
e	.215 BSC		5.45 BSC	
H	.736	.752	18.70	19.10
L	.094	.106	2.40	2.70
L1	.047	.055	1.20	1.40
L2	.039	.045	1.00	1.15
L3	.010 BSC		0.25 BSC	
L4	.150	.161	3.80	4.10



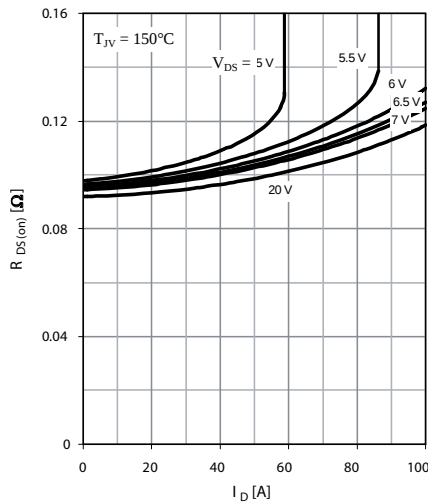


Fig. 4 Typ. drain-source on-state resistance characteristics of IGBT

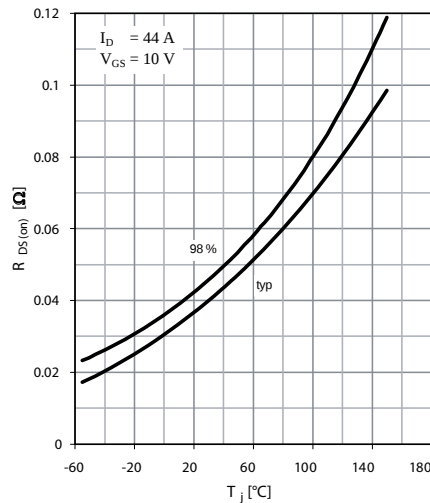


Fig. 5 Drain-source on-state resistance

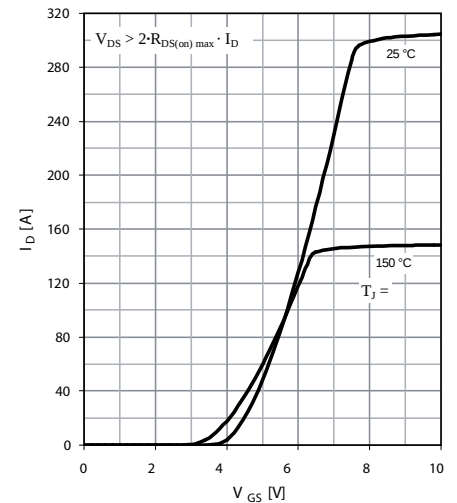


Fig. 6 Typ. transfer characteristics

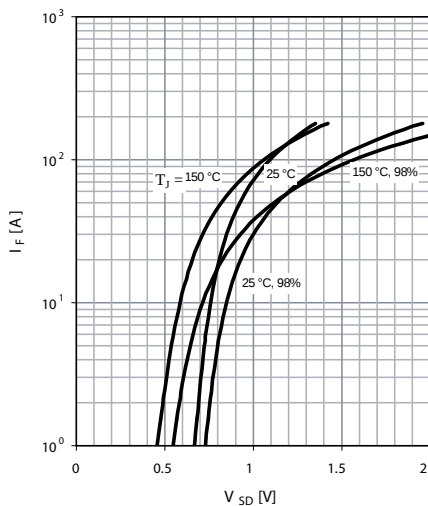


Fig. 7 Forward characteristic of reverse diode

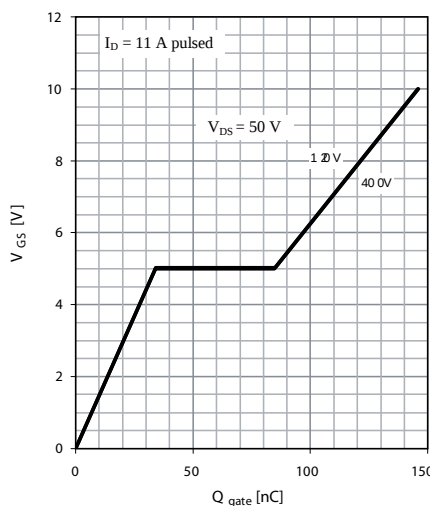


Fig. 8 Typ. gate charge

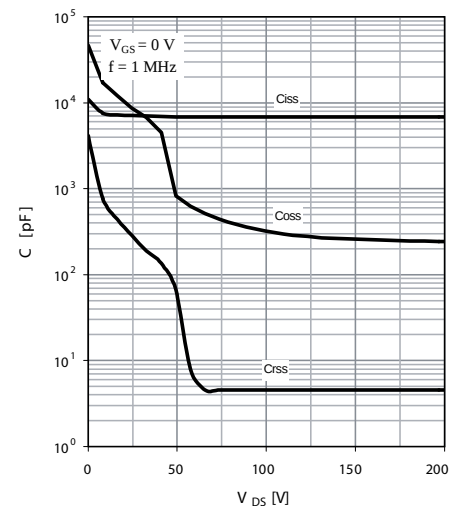


Fig. 9 Typ. capacitances

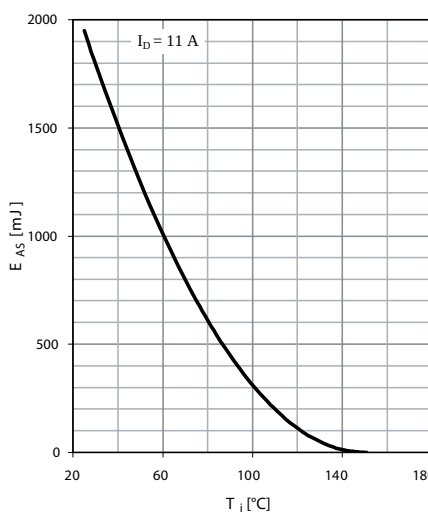


Fig. 10 Avalanche energy

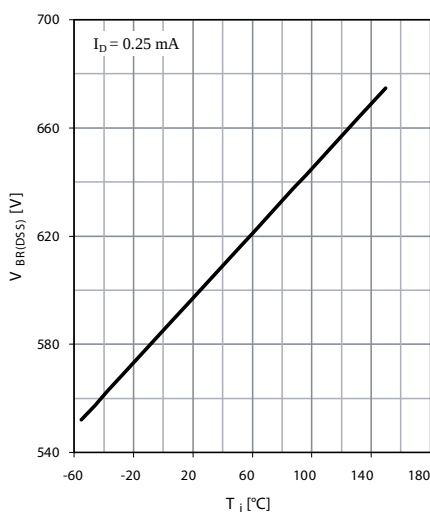


Fig. 11 Drain-source breakdown voltage

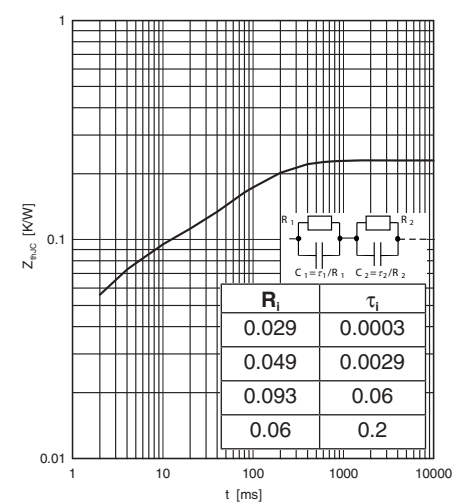


Fig. 12 Max. transient thermal impedance

IXYS reserves the right to change limits, test conditions and dimensions.

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